NPN Silicon Epitaxial Planar Transistor

High voltage fast switching power transistor



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V _{CBO}	700	V
Collector Emitter Voltage	V _{CEO}	400	V
Emitter Base Voltage	V _{EBO}	9	V
Collector Current	I _C	1.5	А
Collector Peak Current (tp < 5 ms)	I _{CM}	3	А
Base Current	I _B	0.75	А
Base Peak Current	I _{BM}	1.5	А
Total Dissipation	P _{tot}	1.1	W
Operating Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	- 65 to + 150	°C

Characteristics at $T_a = 25$ °C

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $V_{CE} = 2 \text{ V}$, $I_C = 0.5 \text{ A}$ at $V_{CE} = 2 \text{ V}$, $I_C = 1 \text{ A}$	h _{FE} h _{FE}	8 5	35 25	
Collector Cutoff Current at V _{CB} = 700 V	I _{CBO}	-	1	mA
Emitter Cutoff Current at V _{EB} = 9 V	I _{EBO}	-	1	mA
Collector Emitter Breakdown Voltage at I _C = 10 mA	V _{(BR)CEO}	400	-	V
Collector Emitter Saturation Voltage at $I_C = 0.5 \text{ A}$, $I_B = 0.1 \text{ A}$ at $I_C = 1 \text{ A}$, $I_B = 0.25 \text{ A}$ at $I_C = 1.5 \text{ A}$, $I_B = 0.5 \text{ A}$	V _{CEsat}	- - -	0.5 1 3	V
Base Emitter Saturation Voltage at $I_C = 0.5 \text{ A}$, $I_B = 0.1 \text{ A}$ at $I_C = 1 \text{ A}$, $I_B = 0.25 \text{ A}$	V _{BEsat}		1 1.2	V



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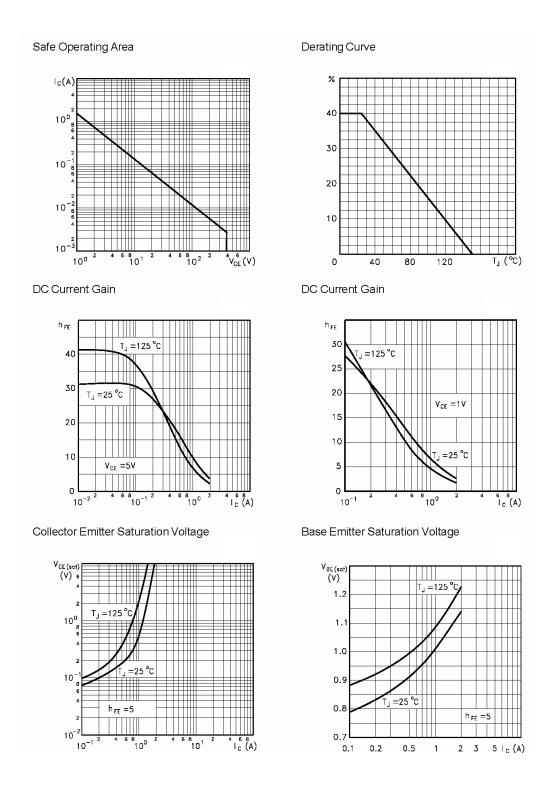
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